

NANOMYTE® PHE-20 ("LAGP")

Physical Characteristics

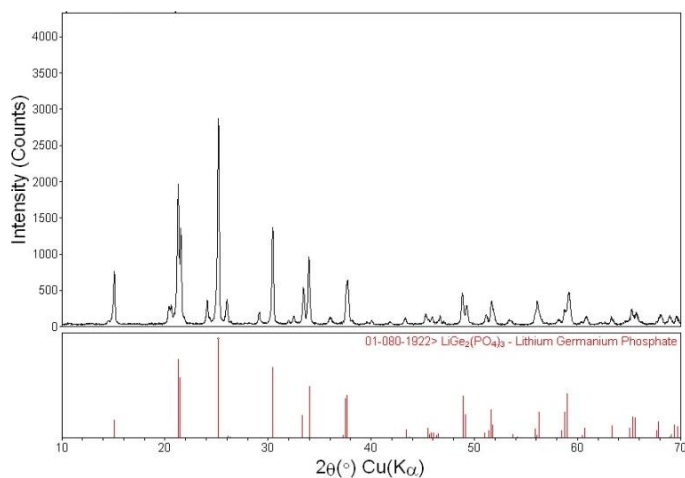
Product Description:	Lithium Aluminum Germanium Phosphate ("LAGP")
Chemical Formula:	$\text{Li}_{1.5}\text{Al}_{0.5}\text{Ge}_{1.5}(\text{PO}_4)_3$
Color:	White
Phase Purity:	> 95%
Average Particle Size (D50):	2 – 3 μm
Crystal Structure:	N/A
Crystal Density:	3.43 g/cm^3
Specific Surface Area:	1.89 m^2/g
Ionic Conductivity:	10^{-5} to 10^{-4} S/cm (unsintered, cold-pressed pellet @ RT)

**Sintered material will have higher ionic conductivity*

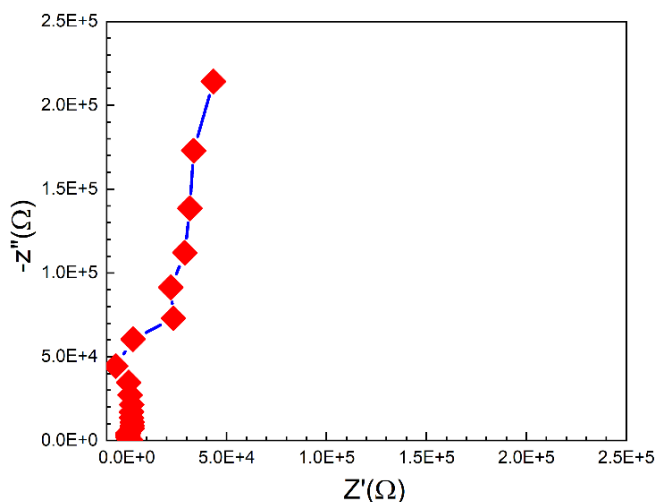
Operating Conditions

Stability Voltage Window:	~ 6.0V vs. Li/Li+
Sensitivity to Air or Moisture:	Stable, but limit exposure to air/ CO_2
Recommended Working Atmosphere:	Air

Characterization Data



X-ray Diffraction (XRD)



Ionic Conductivity

Storage & Handling

Precautions for Safe Handling

Avoid contact with skin and eyes. Avoid formation of dust and aerosols. Provide appropriate exhaust ventilation at places where dust is formed. Appropriate personal protective equipment should be used at all times.

Conditions for Safe Storage

Keep container tightly closed in a dry, well-ventilated place. Store away from oxidizing agents.

Refer to SDS for complete information on the safe handling of this material.

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